

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2SD2550

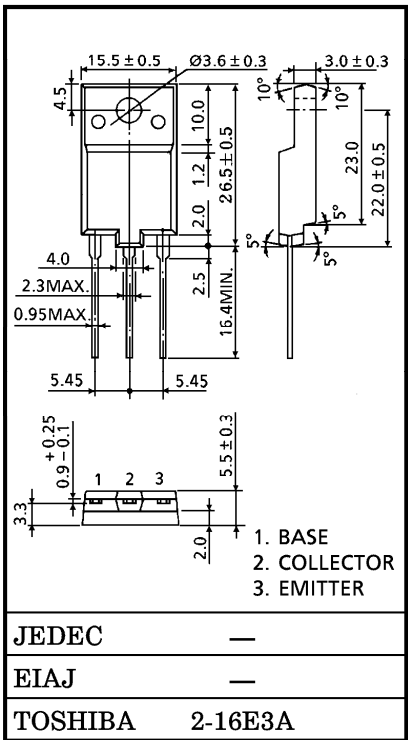
HORIZONTAL DEFLECTION OUTPUT FOR COLOR TV

Unit in mm

- High Voltage : $V_{CBO} = 1700\text{ V}$
- Low Saturation Voltage : $V_{CE(sat)} = 5.0\text{ V (Max)}$
- High Speed : $t_f = 0.6\text{ }\mu\text{s (Max)}$
- Built-in Damper Type
- Collector Metal (Fin) is Fully Covered with Mold Resin.

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

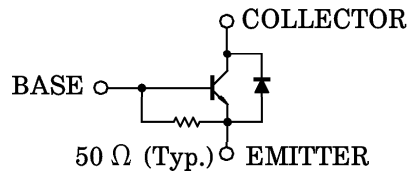
CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	1700	V
Collector-Emitter Voltage		V_{CEO}	600	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC	I_C	4	A
	Pulse	I_{CP}	8	
Base Current		I_B	2	A
Collector Power Dissipation ($T_c = 25^\circ\text{C}$)		P_C	50	W
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	$-55\sim 150$	$^\circ\text{C}$



JEDEC	—
EIAJ	—
TOSHIBA	2-16E3A

Weight : 5.5 g (Typ.)

EQUIVALENT CIRCUIT



961001EAA1

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 1700 \text{ V}, I_E = 0$	—	—	1	mA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 5 \text{ V}, I_C = 0$	66	—	200	mA
Emitter-Base Breakdown Voltage		$V_{(BR) EBO}$	$I_E = 400 \text{ mA}, I_B = 0$	5	—	—	V
DC Current Gain		h_{FE}	$V_{CE} = 5 \text{ V}, I_C = 1 \text{ A}$	8	—	22	—
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 3 \text{ A}, I_B = 0.8 \text{ A}$	—	5	8	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 3 \text{ A}, I_B = 0.8 \text{ A}$	—	—	1.2	V
Forward Voltage (Damper Diode)		$-V_F$	$I_F = 4 \text{ A}$	—	1.5	2.0	V
Transition Frequency		f_T	$V_{CE} = 10 \text{ V}, I_C = 0.1 \text{ A}$	—	3	—	MHz
Collector Output Capacitance		C_{ob}	$V_{CE} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	—	85	—	pF
Switching Time	Storage Time	T_{stg}	$I_{CP} = 3 \text{ A}, I_{B1}(\text{end}) = 0.8 \text{ A}$ $f_H = 15.75 \text{ kHz}$	—	7.5	10	μs
	Fall Time	t_f		—	0.3	0.6	

